Band switching diode

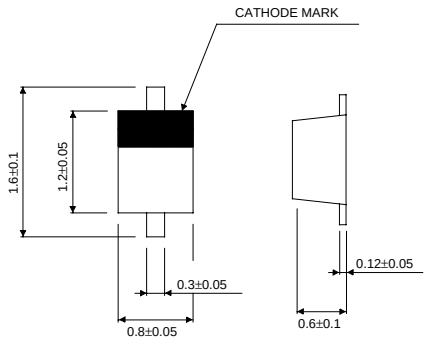
1SS390

●**Applications**
High frequency switching

●**Features**
1) Extremely Small surface mounting type. (EMD2)
2) High reliability.

●**Construction**
Silicon epitaxial planar

●**External dimensions** (Units : mm)



ROHM : EMD2
EIAJ : SC-79
JEDEC : SOD-523

●**Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	35	V
DC forward current	I_F	100	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	−55~+125	°C

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	–	1.0	V	I_F=10mA
Reverse current	I_R	–	–	10	nA	V_R=25V
Capacitance between terminals	C_T	–	–	1.2	pF	V_R=6V, f=1MHz
Forward operating resistance	r_F	–	–	0.9	Ω	I_F=2mA, f=100MHz

●**Electrical characteristic curves** (Ta=25°C)

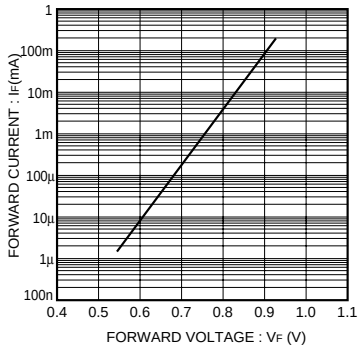


Fig. 1 Forward characteristics

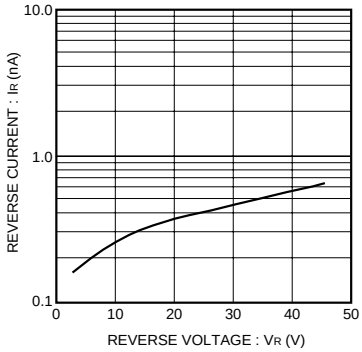


Fig. 2 Reverse characteristics

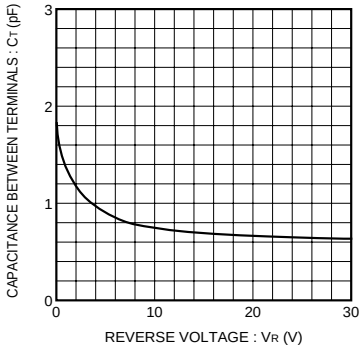


Fig. 3 Capacitance between terminals characteristics

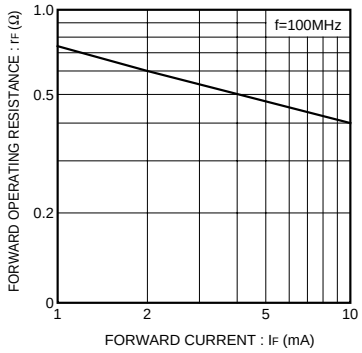


Fig. 4 Forward operating resistance characteristics